TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRIAC

# TLP3041(S),TLP3042(S),TLP3043(S)

OFFICE MACHINE
HOUSEHOLD USE EQUIPMENT
TRIAC DRIVER
SOLID STATE RELAY

The TOSHIBA TLP3041 (S), TLP3042 (S), TLP3043 (S) consist of a zero voltage crossing turn-on photo-triac optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package. All parameters are tested to the specification of TLP3041, TLP3042, TLP3043.

• Peak Off-State Voltage : 400 V (min)

• Trigger LED Current : 15 mA (max) (TLP3041)

10 mA (max) (TLP3042) 5 mA (max) (TLP3043)

• On-State Current : 100 mA (max)

• UL Recognized : UL1577, File No. E67349

• Isolation Voltage : 5000 Vrms (min)

Option (D4) Type

VDE Approved : DIN VDE0884 / 06.92

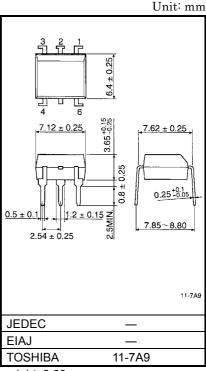
Certificate No. 68329

Maximum Operating Insulation Voltage : 890 Vpk Highest Permissible Over Voltage : 8000 Vpk

Note: When a VDE0884 approved type is needed,please designate the "Option (D4)"

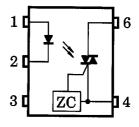
#### • Device Construction

	7.62mm pich	10.16 mm pich			
	standard type	(LF2) type			
Creepage Distance	7.0 mm (min)	8.0 mm (min)			
Clearance	7.0 mm (min)	8.0 mm (min)			
<b>Insulation Thickness</b>	0.5 mm (min)	0.5 mm (min)			



weight: 0.39g

# PIN CONFIGURATION (Top view)



- 1: ANODE
- 2: CATHODE
- 3: N.C.
- 4: TERMINAL 1
- 6: TERMINAL 2



# MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC			SYMBOL	RATING	UNIT
0	Forward Current		ΙF	50	mA
	Forward Current Derati (Ta ≥ 53°C)	ng	ΔI <sub>F</sub> / °C	-0.7	mA / °C
	Peak Forward Current (100 µs pulse, 100 pps)		I <sub>FP</sub>	1	А
LED	Power Dissipation		$P_{D}$	100	mW
	Power Dissipation Dera (Ta ≥ 25°C)	ating	ΔP <sub>D</sub> / °C	-1.0	mW / °C
	Reverse Voltage		V <sub>R</sub>	5	V
	Junction Temperature		Tj	125	°C
	Off-State Output Termi	nal Voltage	$V_{DRM}$	400	V
	On-Stage RMS	Ta = 25°C	I	100	m 1
	Current	Ta = 70°C	I <sub>T(RMS)</sub>	50	- mA
~	On-State Current Derait (Ta ≥ 25°C)	ing	ΔI <sub>T</sub> / °C	-1.1	mA / °C
DETECTOR	Peak On-Stage Curren (100 µs pulse, 120pps)	t	I <sub>TP</sub>	2	А
DET	Peak Nonrepetitive Sur Current (P <sub>W</sub> = 10ms, D		I <sub>TSM</sub>	1.2	А
	Power Dissipation		$P_{D}$	300	mW
	Power Dissipation Dera (Ta ≥ 25°C)	ating	ΔP <sub>D</sub> / °C	-4.0	mW / °C
	Junction Temperature		Tj	115	°C
Stora	ige Temperature Range		T <sub>stg</sub>	−55 ~ 150	°C
Operating Temperature Range			T <sub>opr</sub>	<b>−40 ~ 100</b>	°C
Lead Soldering Temperature (10s)			T <sub>sol</sub>	260	°C
Total Package Power Dissipation			P <sub>T</sub>	330	mW
Total Package Power Dissipation Derating (Ta ≥ 25°C)			ΔP <sub>T</sub> / °C	-4.4	mW / °C
	tion Voltage 1 min., R.H. ≤ 60%)	(Note 1)	BVS	5000	Vrms

Note 1: Device considered a two terminal device: Pins 1, 2 and 3 shorted together and pins 4 and 6 shorted together.

#### **RECOMMENDED OPERATING CONDISTIONS**

CHARACTERISTIC	SYMBOL	MIN	TYP.	MAX	UNIT
Supply Voltage	$V_{AC}$	_	_	120	Vac
Forward Current	I <sub>F</sub> *	15	20	25	mA
Peak On-Stage Current	I <sub>TP</sub>	_	_	1	Α
Operating Temperature	T <sub>opr</sub>	-25	_	85	°C

\*: In the case of TLP3042



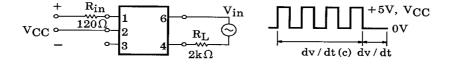
# INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

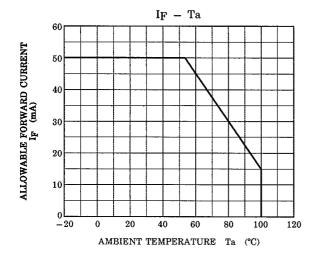
	CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
	Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 10mA	1.0	1.15	1.3	V
LED	Reverse Current	I <sub>R</sub>	V <sub>R</sub> = 5V	_	_	10	μΑ
	Capacitance	C <sub>T</sub>	V = 0, f = 1MHz	_	10	_	pF
	Peak Off-State Current	I <sub>DRM</sub>	V <sub>DRM</sub> = 400V	_	10	100	nA
<u>س</u>	Peak On-Stage Voltage	$V_{TM}$	I <sub>TM</sub> = 100mA	_	1.7	3.0	V
STO	Holding Current	lΗ	_	_	0.6	_	mA
DETECTOR	Critical Rate of Rise of Off- State Voltage	dv / dt	V <sub>in</sub> = 120Vrms, Ta = 85°C (Fig.1)	200	500	_	V/μs
	Critical Rate of Rise of Commutating Voltage	dv / dt(c)	V <sub>in</sub> = 30Vrms, IT = 15mA (Fig.1)	_	0.2	_	V/μs

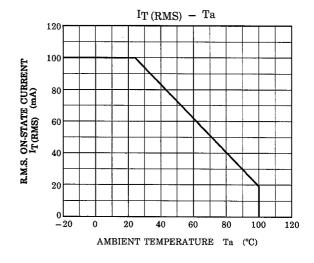
### **COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

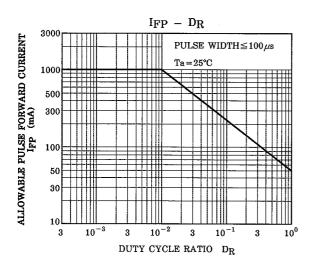
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
	TLP3041	lFT	V <sub>T</sub> = 3V	_	_	15	mA
Trigger LED Current	TLP3042			_	5	10	
	TLP3043			_	_	5	
Inhibit Voltage		V <sub>IH</sub>	I <sub>F</sub> = Rated I <sub>FT</sub>	_	_	40	V
Leakage in Inhibited State		Іін	I <sub>F</sub> = Rated I <sub>FT</sub> V <sub>T</sub> = Rated V <sub>DRM</sub>	_	100	300	μА
Capacitance Input to Output	:	C <sub>S</sub>	V <sub>S</sub> = 0, f = 1MHz	_	0.8	_	pF
Isolation Resistance		R <sub>S</sub>	V <sub>S</sub> = 500V (R.H. ≤ 60%)	5×10 <sup>10</sup>	10 <sup>14</sup>	_	Ω
Isolation Voltage		BV <sub>S</sub>	AC, 1 minute	5000	_	_	Vrms
			AC, 1 second (in oil)	_	10000	_	
			DC, 1 minute (in oil)	_	10000	_	Vdc

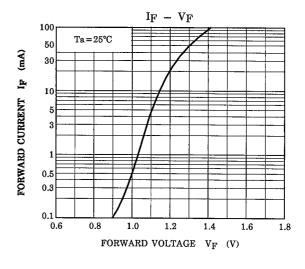
Fig. 1 dv / dt TEST CIRCUIT

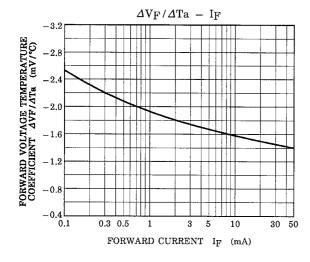


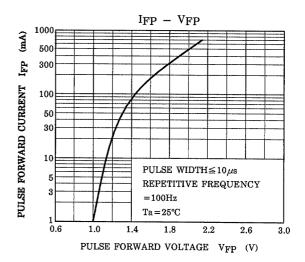




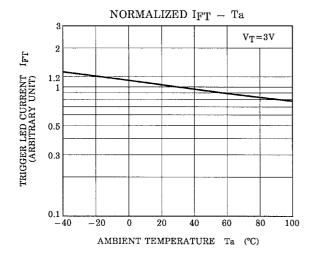


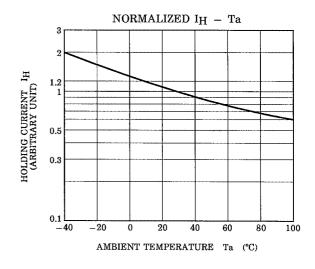


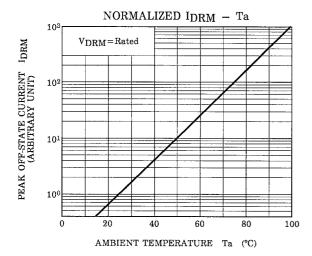


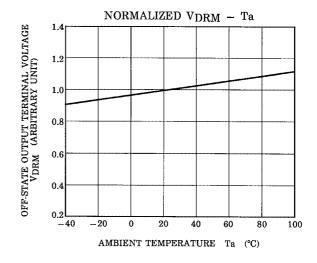


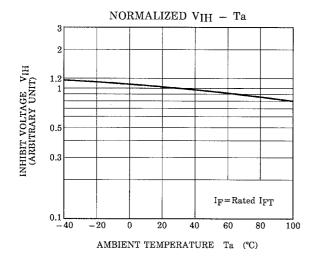
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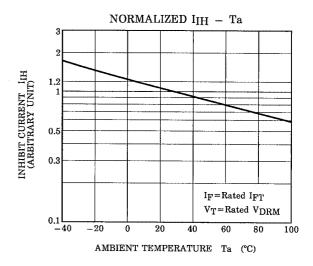












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